

Silicon Epitaxial Planar Diode

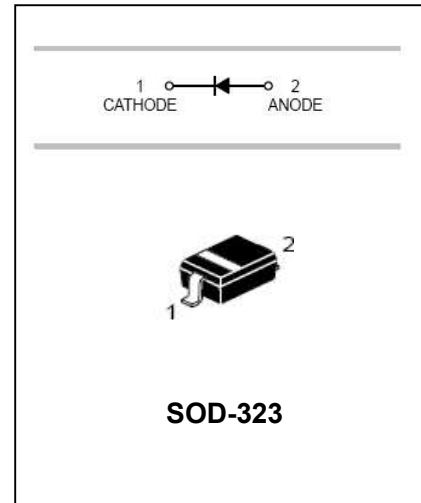
1N4148WS

FEATURES

- Fast Switching Speed:trr=4ns
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance
- Available in Lead Free Version



HF



APPLICATIONS

- Surface mount fast switching diode

ORDERING INFORMATION

Type No.	Marking	Package Code
1N4148WS□	T4	SOD-323

- : none is for Lead Free package;
“G” is for Halogen Free package.

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Average Rectified Output Current	I_o	200	mA
Non-Repetitive Peak Forward Surge Current @t=1.0 μs	I_{FSM}	2.0	A
@t=1.0 s		1.0	
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to+150	°C

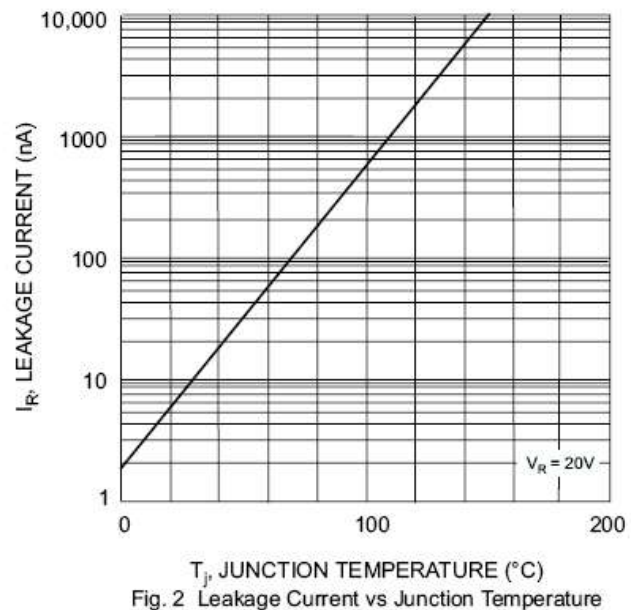
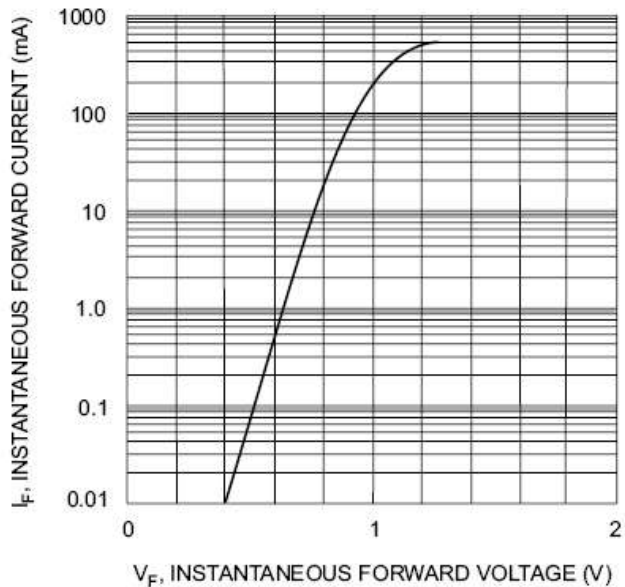
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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V	$I_R=1.0\mu A$
Forward Voltage	V_F	-	0.715 0.855 1.0 1.25	V	$I_F=1.0mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$
Reverse Current	I_R	-	1.0 25	μA nA	$V_R=75V$ $V_R=20V$
Junction Capacitance	C_J	-	2.0	pF	$V_R=0, f=1.0MHz$
Reverse Recovery Time	t_{rr}	-	4.0	ns	$I_F=I_R=10mA,$ $I_{tr}=0.1\times I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



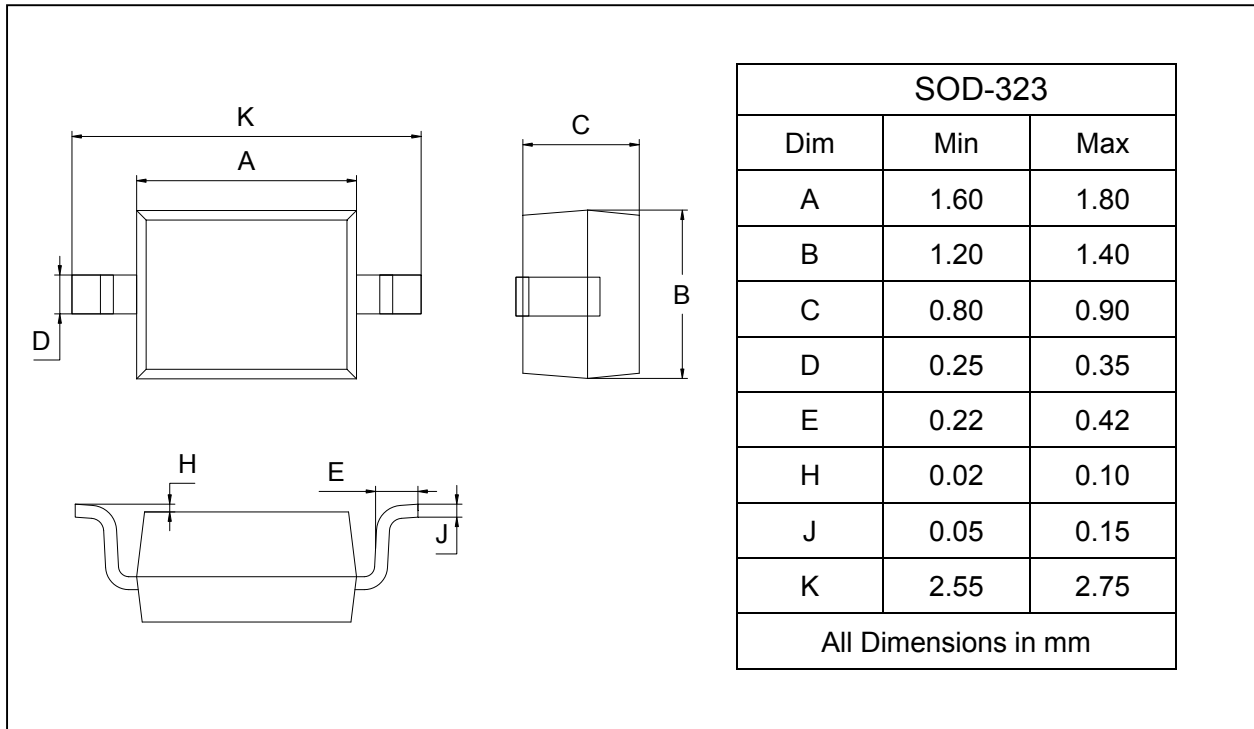
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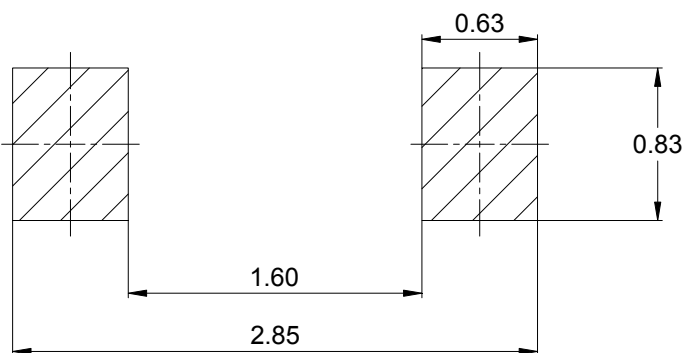
PACKAGE OUTLINE

Plastic surface mounted package

SOD-323



SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
1N4148WS	SOD-323	3000/Tape&Reel